

ABSTRACT

An integrated semiconductor device is provided that has pads with less input signal attenuation. When J-FET (2) is driven by an input signal, the current passing through it varies. The parasitic capacitance (4) is charged or discharged by the input/output signal of the buffer circuit (6) following the varying current. Thus, since the voltage across the parasitic capacitance (3) varies in phase and at the same level, the parasitic capacitance (3) can be ignored. This effect allows attenuation of an input signal due to the parasitic capacitance (3) to be prevented.